

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant :	Shunpei Yamazaki, et al.	Art Unit :	1722
Serial No. :	09/892,225	Examiner :	Mathew J. Song
Filed :	June 25, 2001	Conf. No. :	1969
Title :	SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREFOR		

MAIL STOP AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Applicants request consideration of the references listed on the attached PTO-1449 form. Under 37 C.F.R. § 1.98 (a)(2)(ii), only copies of foreign patent documents and/or non-patent literature are enclosed. Copies of any listed U.S. patents or U.S. patent application publications can be provided upon request.

This statement is being filed after a first Office Action on the merits, but before receipt of a final Office Action or a Notice of Allowance. The fee in the amount of \$180 in payment of the late submission fee of §1.17(p) for the Information Disclosure Statement is being paid concurrently herewith on the Electronic Filing System (EFS) by way of Deposit Account authorization. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: _____

7/10/06



Roberto J. Devoto
Reg. No. 55/108

Fish & Richardson P.C.
Citigroup Center
52nd Floor
153 East 53rd Street
New York, New York 10022-4611
Telephone: (212) 765-5070
Facsimile: (212) 258-2291
30291262.doc

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-279001	Application No. 09/892,225
Information Disclosure Statement by Applicant (Use several sheets if necessary)		Applicant Shunpei Yamazaki, et al.	
		Filing Date June 25, 2001	Group Art Unit 1722

(37 CFR §1.98(b))

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	5,932,893	08/03/1999	Miyazaki et al.			02/03/1998
	AB	5,943,560	08/24/1999	Chang et al.			04/19/1996
	AC	5,977,560	11/02/1999	Banerjee et al.			05/09/1997
	AD	6,087,679	07/11/2000	Yamazaki et al.			07/22/1998
	AE	6,107,654	08/22/2000	Yamazaki			02/08/1999
	AF	6,307,214	10/23/2001	Ohtani et al.			05/27/1998
	AG	6,307,220	10/23/2001	Yamazaki			08/05/1998
	AH	6,335,541	01/01/2002	Ohtani et al.			04/15/1996
	AI	6,346,716	02/12/2002	Yamazaki			12/19/1997
	AJ	6,452,211	09/17/2002	Ohtani et al.			06/09/1998
	AK	6,495,886	12/17/2002	Yamazaki et al.			06/13/2000
	AL	6,610,996	08/26/2003	Yamazaki et al.			08/27/2001
	AM	6,690,068	02/10/2004	Yamazaki et al.			06/06/2001
	AN	6,693,044	02/17/2004	Yamazaki et al.			01/08/1999
	AO	6,787,807	09/07/2004	Yamazaki et al.			06/18/2001
	AP	6,828,587	12/07/2004	Yamazaki et al.			06/14/2001
	AQ	6,956,235	10/18/2005	Yamazaki et al.			04/29/2004
	AR	2002/0008286	01/24/2002	Yamazaki et al.			06/06/2001
	AS	2002/0038889	04/04/2002	Yamazaki et al.			06/18/2001
	AT	2002/0043662	04/18/2002	Yamazaki et al.			06/14/2001
	AU	2004/0108576	06/10/2004	Yamazaki et al.			12/05/2003
	AV	2004/0201022	10/14/2004	Yamazaki et al.			04/29/2004

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AW							
	AX							

Examiner Signature	Date Considered
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Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AY							
	AZ							
	AAA							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	ABB	Haji et al., "Mode of Growth and Microstructure of Polycrystalline Silicon Obtained by Solid-Phase Crystallization of an Amorphous Silicon Film," J. Appl. Phys. 75 (8), April 15, 1994, pages 3944-3952.
	ACC	Hayzelden et al., "Silicide Formation and Silicide-Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," J. Appl. Phys. 73 (12), June 15, 1993, pages 8279-8289.
	ADD	
	AEE	

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